

CLAIM AMENDMENTS

1. (Currently Amended) A semiconductor device comprising:
a substrate;
a metal wiring ~~formed on the substrate and covered with the~~ sandwiched by films of a high-melting-point metal ~~immediately above and below~~; and
an interlayer insulating film, ~~formed by a plasma CVD method so as to cover,~~ covering the metal wiring.

2. (Currently Amended) A semiconductor device comprising:
a substrate;
~~an~~ Al wiring ~~formed on a~~ the substrate;
an Al compound layer ~~formed on the side of the Al wiring~~; and
an interlayer insulating film, ~~formed by a plasma CVD method so as to cover,~~ covering the Al wiring and the Al compound layer.

3. (Currently Amended) The semiconductor device according to claim 2, wherein the Al compound layer ~~is subjected to~~ includes a nitride, produced by annealing the Al wiring in a nitrogen atmosphere to nitrogenize the side of the Al wiring.

4. (Currently Amended) The semiconductor device according to claim 2, wherein the Al compound layer ~~is subjected to~~ includes an oxide, produced by annealing the Al wiring in an oxygen atmosphere to oxidize the side of the Al wiring.

5. (Currently Amended) A semiconductor device comprising:
a substrate;
a metal wiring ~~formed on a~~ the substrate;
a buffer layer ~~formed so as to cover~~ covering the metal wiring; and
an interlayer insulating film ~~formed on the buffer layer, formed by a plasma CVD method.~~

6. (Currently Amended) The semiconductor device according to claim 5, wherein ~~any of an~~ the buffer layer is chosen from the group consisting of SiON film, an SiN film, and an oxide produced by a plasma TEOS film is used as the buffer layer tetraethylorthosilicate process.

In re Appln. of MASAMITSU et al.
Application No. Unassigned

7. (Currently Amended) The semiconductor device according to claim 5, wherein the ~~film~~ thickness of the buffer layer is 50 to 200 nm.